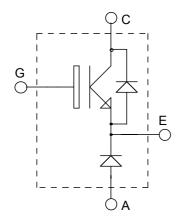


ISOTOP® Buck chopper Trench + Field Stop IGBT3

$$V_{CES} = 1200V$$
  
 $I_{C} = 75A @ Tc = 80°C$ 



#### Application

- AC and DC motor control
- Switched Mode Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration



#### **Benefits**

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### **Absolute maximum ratings**

ISOTOP®

Symbol	Parameter			Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage			1200	V
$I_{C1}$	Continuous Collector Current	$T_C = 25^{\circ}C$	100		
$I_{C2}$	Continuous Conector Current	$T_C = 80$ °C	75	Α	
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	175		
$V_{GE}$	Gate – Emitter Voltage			±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	416	W	
$IF_{AV}$	Maximum Average Forward Current	Duty cycle=0.5	$T_C = 80$ °C	27	A
$IF_{RMS}$	RMS Forward Current (Square wave, 50% duty)			34	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



### All ratings @ $T_j = 25$ °C unless otherwise specified

#### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA
V	Collector Emitter on Voltage	$V_{GE} = 15V$ $I_{C} = 75A$	$T_j = 25$ °C	1.4	1.7	2.1	V
V <sub>CE(on)</sub>	Collector Emitter on Voltage		$T_j = 125$ °C		2.0		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 3mA$		5.0		6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V$ , $V_{CE} = 0V$				500	nA

### **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		5340		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		280		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		240		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching (25°C)		260		ns
$T_{r}$	Rise Time	$V_{GE} = 15V$		30		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$ $R_G = 4.7\Omega$		420		
$T_{\mathrm{f}}$	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	$ \begin{array}{l} \text{Inductive Switching (125°C)} \\ V_{GE} = 15V \\ V_{Bus} = 600V \\ I_{C} = 75A \\ R_{G} = 4.7\Omega \end{array} $		290		
$T_{\rm r}$	Rise Time			45		ns
$T_{d(off)}$	Turn-off Delay Time			520		
$T_{\mathrm{f}}$	Fall Time			90		
$E_{on}$	Turn-on Switching Energy			7		mJ
$E_{\text{off}}$	Turn-off Switching Energy			9.5		1117



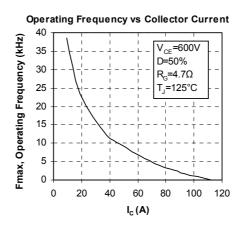
Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 30A$			2.0	2.5	
		$I_F = 60A$					V
		$I_F = 30A$	$T_i = 125$ °C		1.8		İ
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25$ °C			250	μA
1RM	Waximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 125$ °C			500	μΛ
$C_{T}$	Junction Capacitance	$V_R = 200V$			32		pF
	Reverse Recovery Time	$I_F=1A, V_R=30V$ di/dt =100A/\(\mu\)s	$T_j = 25$ °C		31		
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $T_i = 125^{\circ}C$ $T_i = 25^{\circ}C$	$T_i = 25^{\circ}C$		370		ns
			$T_{i} = 125^{\circ}C$		500		
$I_{RRM}$	Maximum Reverse Recovery Current		$T_j = 25$ °C		5		Α
1RRM	Waximum Reverse Recovery Current	$V_R = 800V$	$T_{i} = 125^{\circ}C$		12		А
0	Payanga Pagayany Changa	$di/dt = 200A/\mu s$	$T_j = 25$ °C		660		nC
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		3450		пС
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 1000A/\mu s$			220		ns
$Q_{rr}$	Reverse Recovery Charge		$T_j = 125$ °C		4650		nC
$I_{RRM}$	Maximum Reverse Recovery Current				37		A

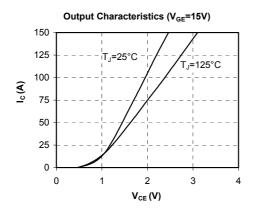
Thermal and package characteristics

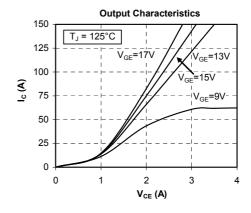
Symbol	Characteristic		Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance  IGBT  Diode	IGBT			0.3	°C/W
KthJC		Diode			1.1	
$R_{thJA}$	Junction to Ambient (IGBT & Diode)				20	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz		2500			V
$T_J, T_{STG}$	Storage Temperature Range		-55		150	°C
$T_{ m L}$	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	C
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4m	m Machine)			1.5	N.m
Wt	Package Weight			29.2		g

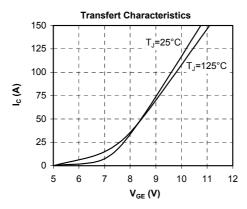
### **Typical IGBT Performance Curve**

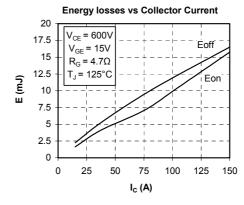


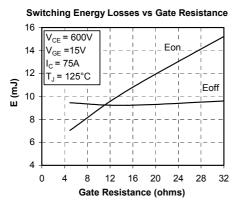


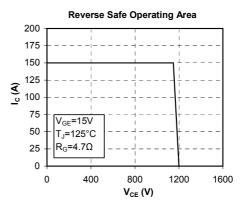


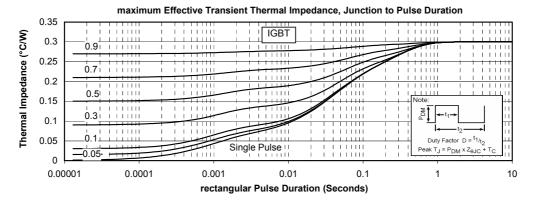














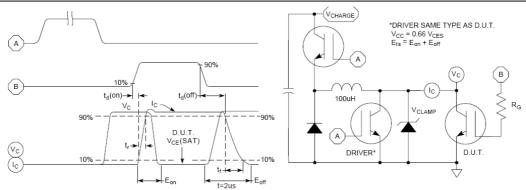


Figure 15, Switching Loss Test Circuit and Waveforms

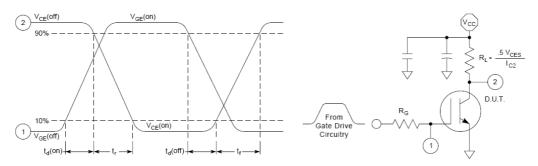
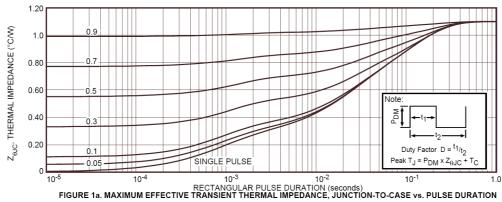


Figure 16, Resistive Switching Time Test Circuit and Waveforms

#### **Typical Diode Performance Curve**



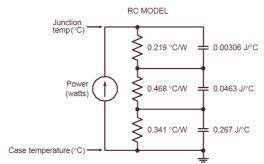


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL



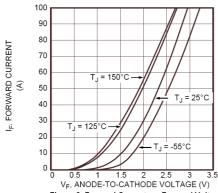


Figure 2. Forward Current vs. Forward Voltage

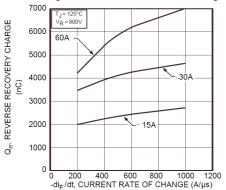


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

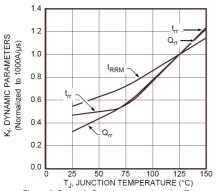


Figure 6. Dynamic Parameters vs. Junction Temperature

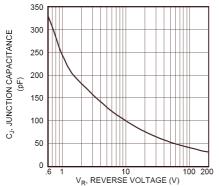


Figure 8. Junction Capacitance vs. Reverse Voltage

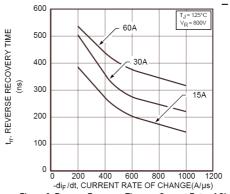


Figure 3. Reverse Recovery Time vs. Current Rate of Change

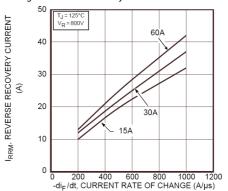


Figure 5. Reverse Recovery Current vs. Current Rate of Change

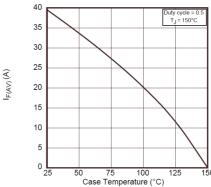


Figure 7. Maximum Average Forward Current vs. CaseTemperature



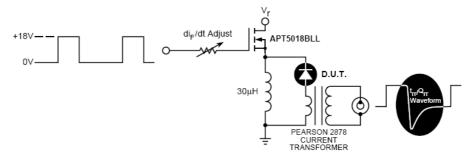


Figure 9. Diode Test Circuit

I I F - Forward Conduction Current

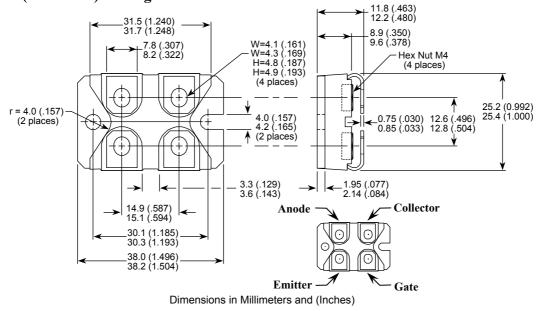
I dip/dt - Rate of Diode Current Change Through Zero Crossing.

I RRM - Maximum Reverse Recovery Current.

I trr - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I RRM and 0.25 I RRM passes through zero.

Figure 10, Diode Reverse Recovery Waveform and Definitions

### **SOT-227 (ISOTOP®) Package Outline**



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